

## **Features**

- RoHS compliant\*
- Reverse voltage from 20 to 60 V
- Forward current of 1 A
- High current capability



 For use in low voltage high frequency inverters, free wheeling and polarity protection applications

## CD214B-B120 ~ B160 Schottky Barrier Rectifier Chip Diode

#### **General Information**

The markets of portable communications, computing and video equipment are challenging the semiconductor industry to develop increasingly smaller electronic components.

Bourns offers Schottky Rectifier Diodes for rectification applications, in compact chip package DO-214AA (SMB) size format, which offer PCB real estate savings and are considerably smaller than most competitive parts. The Schottky Rectifier Diodes offer a forward current of 1 A with a choice of repetitive peak reverse voltage of 20 V up to 60 V.

Bourns® Chip Diodes conform to JEDEC standards, are easy to handle with standard pick and place equipment and their flat configuration minimizes roll away.

#### Electrical Characteristics (@ TA = 25 °C Unless Otherwise Noted)

Parameter.	Completed	CD214B-					11
Parameter	Symbol	B120	B130	B140	B150	B160	Unit
Maximum Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	20	30	40	50	60	V
Maximum RMS Voltage	V <sub>RMS</sub>	14	21	28	35	42	V
Maximum DC Blocking Voltage	V <sub>DC</sub>	20	30	40	50	60	V
Maximum Average Forward Rectified Current <sup>1</sup>	I <sub>(AV)</sub>			1			А
DC Reverse Current @ Rated DC Blocking Voltage (@TA = 25 °C)	IR			0.5			mA
DC Reverse Current @ Rated DC Blocking Voltage (@TA = 100 °C)	IR	10			mA		
Typical Junction Capacitance 2	င၂	110			pF		
Maximum Instantaneous Forward Voltage @ 1 A	V <sub>F</sub>	0.5 0.7		.7	V		
Typical Thermal Resistance <sup>3</sup>	$R_{\theta JA}$	22			°C/W		
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	30			A		

#### Notes:

- 1 See Forward Derating Curve.
- 2 Measured at 1 MHz and an applied reverse voltage of 4.0 V.
- 3 Thermal resistance from junction to ambient and from junction to lead P.C.B. mounted on 0.2 x 0.2 " (5.0 x 5.0 mm) copper pad areas.

## Thermal Characteristics (@ T<sub>A</sub> = 25 °C Unless Otherwise Noted)

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Parameter	Symbol	B120	B130	B140	B150	B160	Unit
Operating Temperature Range	TJ		-55 to +125		-55 to	+150	°C
Storage Temperature Range	TSTG			-55 to +150			°C

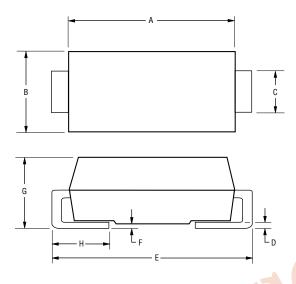
The device characteristics and parameters in this data sheet can and do vary in different applications and actual device performance may vary over time. Users should verify actual device performance in their specific applications.

<sup>\*</sup>RoHS Directive 2002/95/EC Jan. 27, 2003 including annex and RoHS Recast 2011/65/EU June 8, 2011. Specifications are subject to change without notice.

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## BOURNS®

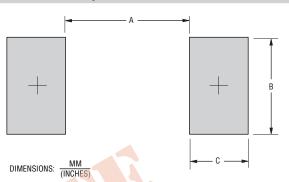
#### **Product Dimensions**



Dimension	SMB (DO-214AA)		
Α	4.06 - 4.57		
	(0.160 - 0.180)		
В	3.30 - 3.94		
_ B	(0.130 - 0.155)		
С	1.96 - 2.21		
	(0.078 - 0.087)		
D	0.15 - 0.31		
	(0.006 - 0.112)		
E	5.21 - 5.59		
_	(0.205 - 0.220)		
F	0.05 - 0.20		
	(0.002 - 0.008)		
G	2.01 - 2.62		
4	(0.080 - 0.103)		
н	0.76 - 1.52		
П	(0.030 - 0.060)		
	1		

DIMENSIONS:  $\frac{MM}{(INCHES)}$ 

#### **Recommended Pad Layout**



Dimension	SMA (DO-214AC)
А	2.90 (0.114)
В	<u>3.00</u> (0.118)
С	<u>2.30</u> (0.091)

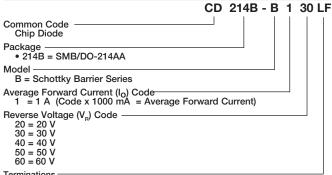
### **Physical Specifications**

Case	Molded plastic
	Indicated by cathode band
-	0.003 ounces / 0.093 grams

## **Typical Part Marking**

CD214B-B120	B	120E
CD214B-B130	B	130E
CD214B-B140	B	140E
CD214B-B150	B	150B
CD214B-B160	B	160E

#### **How To Order**



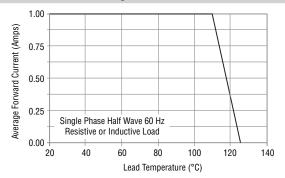
Terminations — LF = 100 % Sn (RoHS Compliant)

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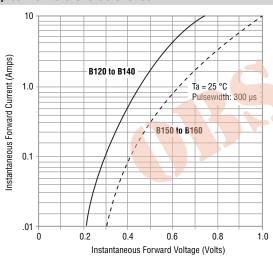
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#### **Rating and Characteristic Curves**

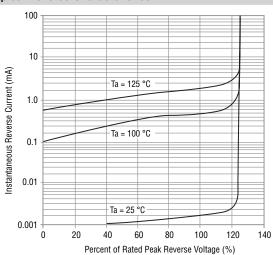
#### **Forward Current Derating Curve**



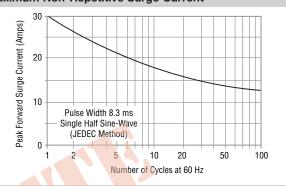
#### **Typical Forward Characteristics**



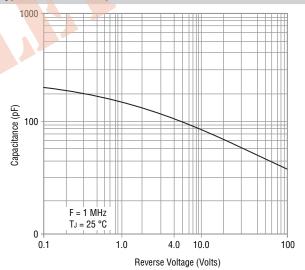
### **Typical Reverse Characteristics**



## **Maximum Non-Repetitive Surge Current**



### **Typical Junction Capacitance**



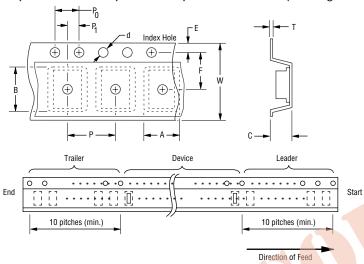
Specifications are subject to change without notice.

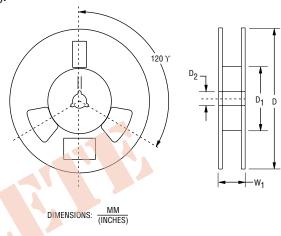
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# CD214B-B120 ~ B160 Schottky Barrier Rectifier Chip Diode **BOURNS**

#### **Packaging Information**

The product will be dispensed in Tape and Reel format (see diagram below).





Devices are packed in accordance with EIA standard RS-481-A and specifications shown here.

Item	Symbol	SMB (DO-214AA)
Carrier Width	A	$\frac{4.94 \pm 0.10}{(0.194 \pm 0.004)}$
Carrier Length	В	$\frac{5.57 \pm 0.10}{(0.219 \pm 0.004)}$
Carrier Depth	С	$\frac{2.36 \pm 0.10}{(0.093 \pm 0.004)}$
Sprocket Hole	d	$\frac{1.55 \pm 0.05}{(0.061 \pm 0.002)}$
Reel Outside Diameter	D	<u>330</u> (12.992)
Reel Inner Diameter	D <sub>1</sub>	50.0 (1.969) MIN.
Feed Hole Diameter	D <sub>2</sub>	$\frac{13.0 \pm 0.20}{(0.512 \pm 0.008)}$
Sprocket Hole Position	E	$\frac{1.75 \pm 0.10}{(0.069 \pm 0.004))}$
Punch Hole Position	F	$\frac{5.50 \pm 0.05}{(0.217 \pm 0.002)}$
Punch Hole Pitch	Р	$\frac{4.00 \pm 0.10}{(0.157 \pm 0.004)}$
Sprocket Hole Pitch	P <sub>0</sub>	$\frac{4.00 \pm 0.10}{(0.157 \pm 0.004)}$
Embossment Center	P <sub>1</sub>	$\frac{2.00 \pm 0.05}{(0.079 \pm 0.002)}$
Overall Tape Thickness	Т	$\frac{0.30 \pm 0.10}{(0.012 \pm 0.004)}$
Tape Width	w	$\frac{12.00 \pm 0.20}{(0.472 \pm 0.008)}$
Reel Width	W <sub>1</sub>	18.4 (0.724) MAX.
Quantity per Reel		3,000

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